

AMENDMENTS

In the Claims:

1. (Thrice Amended) A method of forming a fluorine doped insulating material comprising:

providing a substrate within a reaction chamber, the reaction chamber controlled within a range of temperatures from above 400 degrees Celsius ($^{\circ}\text{C}$) but not greater than about 700°C ;

providing reactants comprising silicon, fluorine and ozone within the reaction chamber; and

depositing an insulating material, at a rate of from about 1000 angstroms per minute ($\text{\AA}/\text{min}$) to about 10000 $\text{\AA}/\text{min}$, comprising fluorine, silicon and oxygen onto the substrate from the reactants, wherein the depositing occurs with a plasma being present in the reaction chamber.

Please cancel Claims 3 and 11 without prejudice.

In Claim 18, replace "700" with --630--.

In Claim 20, replace "without" with --with--.

Please cancel Claim 21 without prejudice.

In Claim 22, replace "21" with --15--.

Sub 251
C2
23. (Thrice Amended) The method of Claim 1 wherein
providing reactants comprising silicon, fluorine and ozone within the
reaction chamber comprise providing reactants comprising triethoxy
fluorosilane, a phosphorus-containing precursor and ozone, wherein the
insulating material deposited is a phosphorus-doped silicon oxide material
having Si-F bonds[, and the depositing occurring without a plasma being
present in the reaction chamber].

Sub 251
C3
25. (Thrice Amended) The method of Claim 1 wherein
providing reactants comprising silicon, fluorine and ozone within the
reaction chamber comprises providing reactants that include triethoxy
fluorosilane, a boron-containing precursor, a phosphorus-containing
precursor and ozone, wherein the insulating material deposited is a boron
and phosphorus-doped silicon oxide material having Si-F bonds[, and the
depositing occurring without a plasma being present in the reaction
chamber].

18 Please cancel Claims 35 and 37 without prejudice.

Sub 251
C4
38. The method of claim 18 comprising maintaining a pressure
and a temperature within the reaction chamber at from about 400 Torr
to about 1 atmosphere and in excess of 500°C but less than 630°C,
respectively, during the depositing.

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In Claim 39, replace "18" with --38--.

Please cancel Claims 40-42 without prejudice.